



Product Summary

BV _{DSS}	Rds(on)	Ι _D T _A = +25°C
-30V	95mΩ @ V _{GS} = -10V	-2.8A
-307	140mΩ @ V_{GS} = -4.5V	-2.3A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- **DC-DC** Converters
- **Power Management Functions**

DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

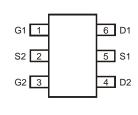
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

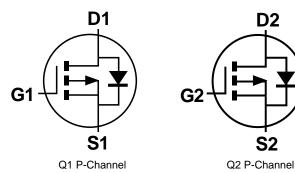
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.013 grams (Approximate)



Top View



Top View



Ordering Information (Note 4)

	Part Number	Case	Packaging				
	DMP3164LVT-7	TSOT26	3,000 / Tape & Reel				
	DMP3164LVT-13	TSOT26	10,000 / Tape & Reel				
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.						

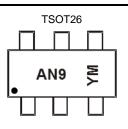
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



AN9 = Product Type Marking Code YM = Date Code Marking \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Data Coda Kav

Date Code Key												
Year	201	9	2020		2021	20	22	2023		2024	2	2025
Code	G		Н				J	K		L		М
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-30	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current (Note 6) V_{GS} = -4.5V	I _D	-2.8 -2.2	А
Maximum Continuous Body Diode Forward Current (Note	ls	-1.0	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-16	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	0.83	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 5)	R _{0JA}	151	°C/W
Power Dissipation (Note 6)	PD	1.16	W
Thermal Resistance, Junction to Ambient $@T_A = +25^{\circ}C$ (Note 6)	R _{0JA}	108	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

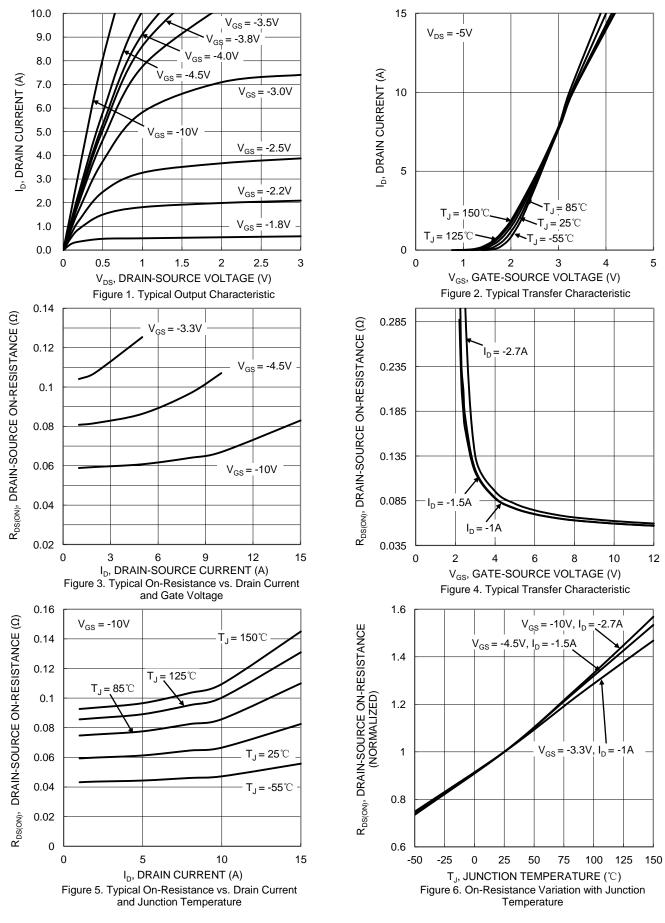
Characteristic	Symbol	Min	Turn	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Symbol		Тур	WIAX	Unit	Test condition	
· · · · · · · · · · · · · · · · · · ·	D)/	20	1	1	V		
Drain-Source Breakdown Voltage	BV _{DSS}	-30		—		$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS		—	-1.0	μA	$V_{DS} = -24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)				•			
Gate Threshold Voltage	V _{GS(TH)}	-0.7	-1.1	-2.1	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$	
			60	95		$V_{GS} = -10V, I_D = -2.7A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	81	140	mΩ	V _{GS} = -4.5V, I _D = -1.5A	
	. ,		104	300		V _{GS} = -3.3V, I _D = -1A	
Diode Forward Voltage	V _{SD}	_	-0.8	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	324	—			
Output Capacitance	Coss	_	44	—	pF	$V_{DS} = -15V, V_{GS} = 0V,$ f = 1.2MHz	
Reverse Transfer Capacitance	C _{rss}	_	33	_			
Gate Resistance	R _q	_	7.2	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	4.4	—		$V_{DS} = -15V, V_{GS} = -4.5V, I_{D} = -3A$	
Total Gate Charge (V _{GS} = -10V)	Qq	_	8.6	—			
Gate-Source Charge	Q _{gs}	_	0.3	—	nC	V _{DS} = -15V, V _{GS} = -10V, I _D = -3A	
Gate-Drain Charge	Q _{qd}	_	1.5	_			
Turn-On Delay Time	t _{D(ON)}	_	7.7	—			
Turn-On Rise Time	t _R	_	17.8	—		$V_{GS} = -10V, V_{DS} = -15V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	17.8	—	ns	$R_G = 6\Omega, R_L = 15\Omega$	
Turn-Off Fall Time	tF	_	29.5	—			

Notes:

Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.

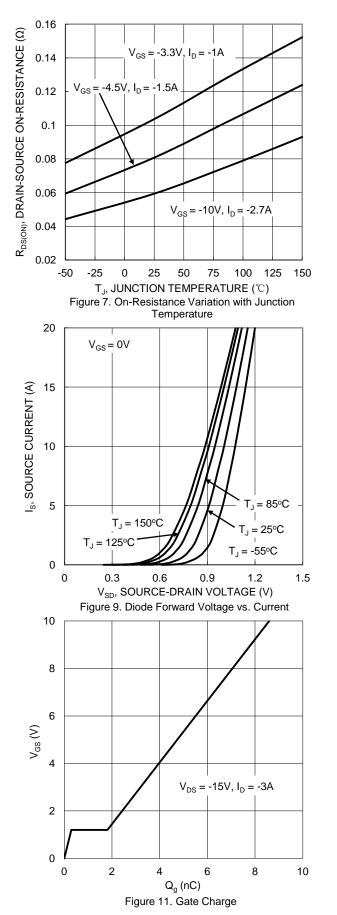


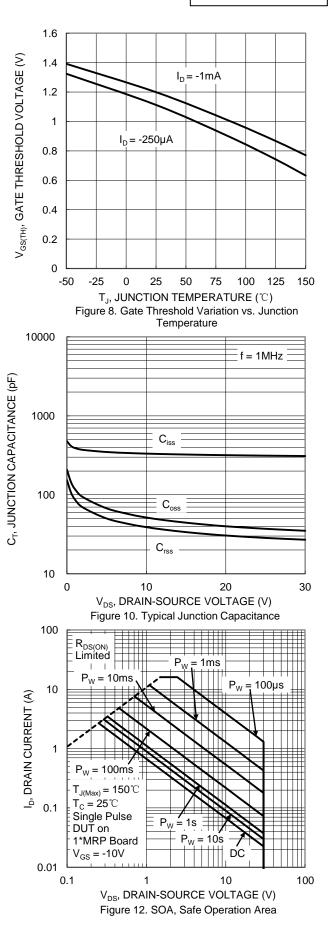
DMP3164LVT



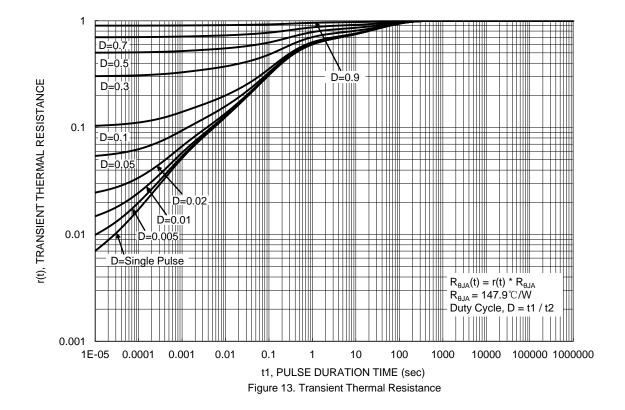
DMP3164LVT Document number: DS41715 Rev. 2 - 2 3 of 7 www.diodes.com









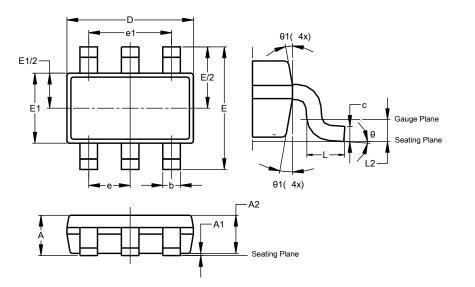




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

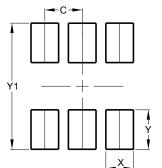
TSOT26



	TSOT26							
Dim	Min	Max	Тур					
Α	-	1.00	-					
A1	0.010	0.100	-					
A2	0.840	0.900	-					
D	2.800	3.000	2.900					
E	2	.800 BS	С					
E1	1.500	1.500 1.700 1.60						
b	0.300	0.450	-					
С	0.120	0.200	-					
е	0.950 BSC							
e1	1	.900 BS	С					
L	0.30	0.50	-					
L2	0	.250 BS	С					
θ	0°	8°	4°					
θ1	4°	12°	-					
A	II Dimen	sions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



TSOT26

Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199



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